Ordering number:EN2372

DSA12T

Diffused Junction Type Silicon Diode

1.2A Power Rectifier

Features

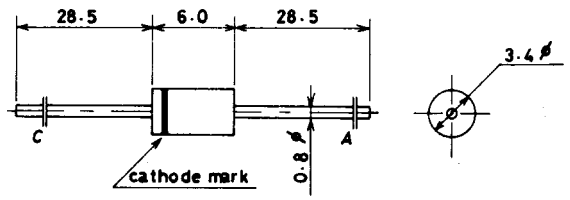
- Plastic molded structure.
- Peak Reverse Voltage : V_{RM}=100 to 1000V
- Average rectified current : I_O=1.2A.

Package Dimensions

unit:mm

1083

[DSA12T]



C:Cathode
A:Anode

Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	DSA12TB	DSA12TC	DSA12TE	Unit
Peak Reverse Voltage	V_{RM}		100	200	400	V
Average Rectified Current	I_O	Ta=60˚C	→	→	1.2	A
Surge Forward Current	I_{FSM}	50Hz sine wave, 1 cycle	→	→	110	A
Junction Temperature	Tj		→	→	150	˚C
Sotrage Temperature	Tstg		→	→	–40 to +150	˚C

Parameter	Symbol	Conditions	DSA12TG	DSA12TJ	DSA12TL	Unit
Peak Reverse Voltage	V_{RM}		600	800	1000	V
Average Rectified Current	I_O	Ta=50˚C	→	→	1.2	A
Surge Forward Current	I_{FSM}	50Hz sine wave, 1 cycle	→	→	70	A
Junction Temperature	Tj		→	→	150	˚C
Storage Temperature	Tstg		→	→	–40 to +150	˚C

Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Forward Voltage	V_F	I_F=1.2A(B, C, E)			1.0	V
		I_F=1.2A(G, J, L)			1.1	V
Reverse Current	I_R	V_R:At each V_{RM}			10	μA